

PTO/SB/08A (08-03)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	10/678,438
Filing Date	3 October 2003
First Named Inventor	Vladimir V. MAKAROV
Art Unit	
Examiner Name	
Attorney Docket Number	65.0395

Sheet 1 of 5

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
SA		US- 5,840,630	11-24-1998	Cecere et al.	
		US- 6,514,866 B2	02-04-2003	Russell et al.	
		US- 2003/0060048 A1	03-27-2003	Russell et al.	
		US- 2003/0038113 A1	02-27-2003	Makarov et al.	
		US- 6,407,001 B1	06-18-2002	Scott	
		US- 6,509,276 B2	01-21-2003	Scott	
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		US- 2002/0195422 A1	12-26-2002	Sievers et al.	
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		US- 5,336,363	08-09-1994	Morita	
		US- 5,140,164	08-18-92	Talbot et al.	
		US- 5,616,921	04-01-97	Talbot et al.	
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		US- 5,851,413	12-22-1998	Casella et al.	
✓		US- 5,899,740	05-04-1999	Kwon	
SA		US- 5,959,358	09-28-1999	Lanford et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
SA		JP2295117	12-06-1990	NTT ✓		✓
SA		JP4173988	11-02-1990	Nissin Electric ✓		✓

Examiner
Signature

Shamim Ahmed

Date
Considered

6/22/05

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Signature**

Shamim Ahmed

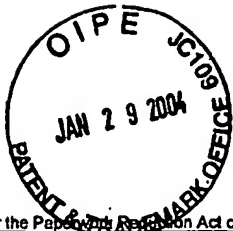
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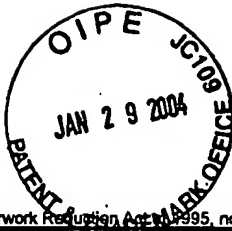
NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SA		S. Herschbein et al., The Challenges of FIB Chip Repair & Debug Assistance in the 0.25 um Copper Interconnect Millenium, Proceedings from 24th International Symposium for Testing and Failure Analysis, 15-19 November 1998, Dallas, Texas, pp.127-130	
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		H. Ximen et al., Halogen-Based Selective FIB Milling for IC Probe-Point Creation and Repair, Proceedings from 20th International Symposium for Testing and Failure Analysis, 1994, pp. 141-145.	
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		P. Ho et al., Overview on Low Dielectric Constant Materials for IC Applications, in Low Dielectric Constant Materials for IC Applications, Ed. by P. Ho et al., Springer-Verlag, Berlin, Heidelberg 2003, Chapter I, pp. 1-21	
SA		J. Gonzalez et al., Chemically enhanced focused ion beam micromachining of copper, J. Vac. Sci. Technol. B 19(6), Nov/Dec 2001, pp. 2539-2542	

Examiner Signature	Shamim Ahmed	Date Considered	6/22/05
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NON PATENT LITERATURE DOCUMENTS

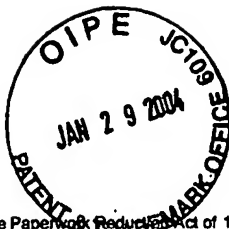
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SA		J. Gonzalez et al, Improvements in Focused Ion Beam Micro-machining of Interconnect Materials, J. Vac. Sci. Technol. B20(6), Nov/Dec 2002, pp. 2700-2704	
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		Y. Igarashi et al., Dry Etching Technique for Subquarter-Micron Copper Interconnects, J. Electronchem. Soc., Vol. 142, No. 3, March 1995, pp. L36-L37	
✓		S. Pauthner, Device modification and gass assisted etching on Cu-samples, 3rd European FIB Users Group Meeting (EFUG99) Abstracts 4 October 1999 (1 paragraph abstract of 8-page document)	
SA		2-Nitroethanol Material Safety Data Sheet, Aldrich Chemical Co., Inc., valid 02/2003-04/2003, (four pages)	

Examiner Signature	Shamim Ahmed	Date Considered	6/22/05
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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SA		N. Goldblatt et al., Unique and Practical IC Timing Analysis Tool Utilizing Intrinsic Photon Emission, Microelectronics Reliability Conference, 2001, 41(9-10): 1507-1512 ✓	
		D. Knebel et al., Diagnosis and Characterization of Timing-Related Defects by Time-Dependent Light Emission, IEEE International Test Conference, 1998, pp. 733-739 ✓	
		T. Lundquist et al., Ultra-Thinning of C4 Integrated Circuits for Backside Analysis during First Silicon Debug, Microelectronics Reliability Conference, 2001, 41(9-10): 1545-1549 ✓	
		T. Lundquist et al., Characterize Gate-Level Transistor Performance with PICA, Semiconductor International, 2001, 4 pages ✓	
SA		C. Musil et al., Focused Ion Beam Microsurgery for Electronics, IEEE Electron Device Letters, 1986, EDL-7(5):285-287 ✓	

Examiner Signature	Shamin Ahmed	Date Considered	6/22/05
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